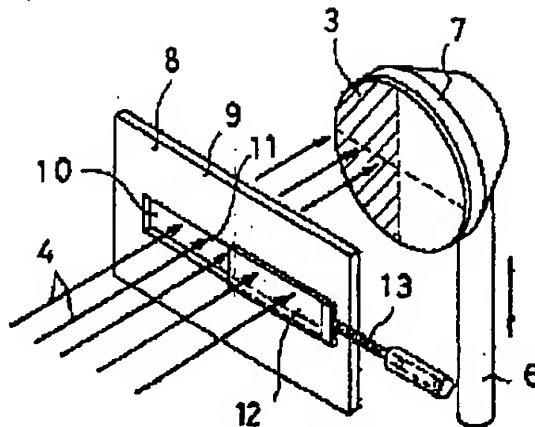


Patent Abstracts of Japan

TITLE : ION IMPLANTATION EQUIPMENT



SOLUTION: In this ion implantation equipment for implanting ions in a substrate 3 disposed in vacuum by scanning an ion beam 4 from an ion source in one direction, an incident area controlling slit 8 for controlling an area on which the ion beam 4 is incident in the plane of the substrate 3 is provided in front of the substrate 3. The incident area controlling slit 8 is composed of a slit 11 having a constant opening space and a shutter 12 for decreasingly controlling the opening space of the slit 11.

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